Electronic Supplementary Information

SiTe Monolayers: Si-Based Analogues of Phosphorene

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Fig. S1 Snapshots depicting structural changes in $\alpha$-SiTe (a-c) and $\beta$-SiTe (d-f) monolayers in the AIMD simulations at 300K. The initial and final geometries are shown in (a) and (c) for $\alpha$-SiTe monolayer, and (d) and (f) for $\beta$-SiTe monolayer, respectively.